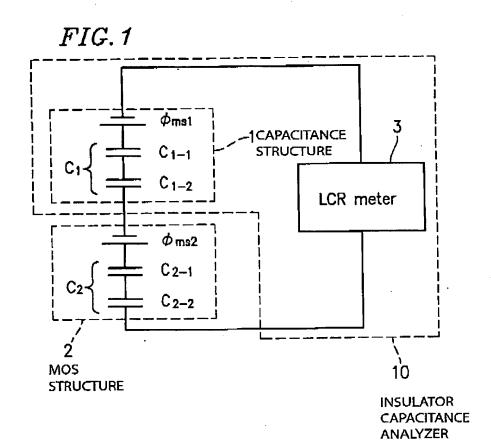
Fax: 703-816-4100 SN 10/203/259/Sheet 1 of 9 Atty, Dkt: 829-593 REPLACEMENT SHEET



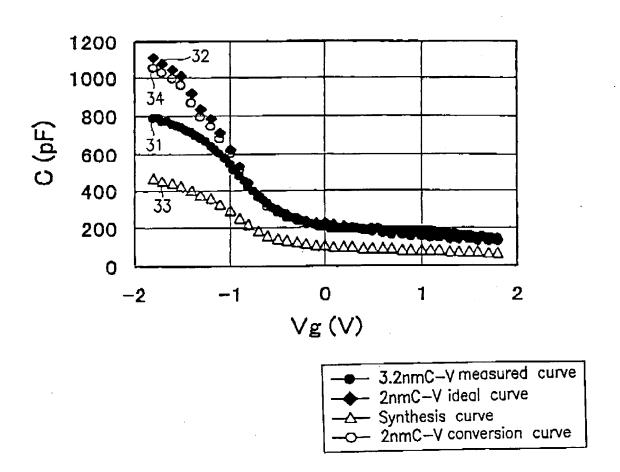
Fax: 703-816-4100 INVENTION: OFFICIAL OFFI SN 10/003258/Sheet 2 of 9 Atty. Dkt.: 829-593 REPLACEMENT SHEET

$$FIG.2 \\ \begin{array}{c|c} & & & \\ \hline & & \phi_{ms1} \\ \hline & & C_{1-1} \\ \hline & & C_{1-2} \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline & & C_{1-2} \\ \hline & & C_{2-1} \\ \hline & & C_{2-2} \\ \end{array} \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline & & \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline & & \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline & & \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline & & \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline & & \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline & & \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline & & \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline & & \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline & & \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline & & \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline & & \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline \end{array} \\ \begin{array}{c|c} & & \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline \end{array} \\ \begin{array}{c|c} & & \\ \end{array} \\ \begin{array}{c|c} & & \\ \hline \end{array} \\ \begin{array}{c|c} & & \\ \end{array} \\ \end{array} \\ \begin{array}{c|c} & & \\ \end{array} \\ \end{array}$$

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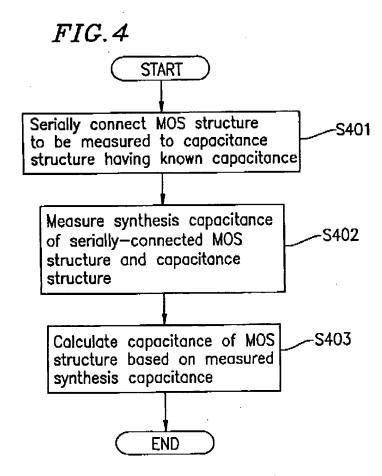
FIG. 3

NMOS C-V Characteristics

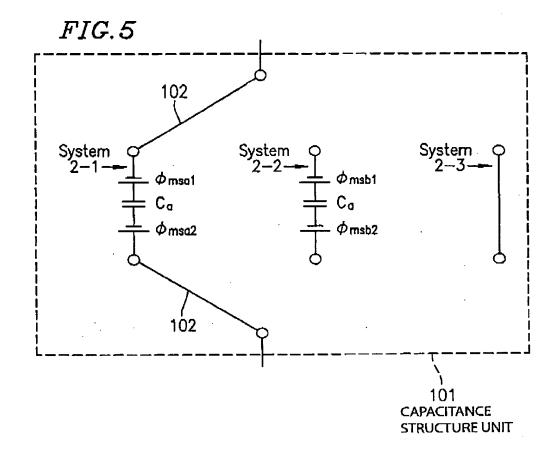


NIXON & VANDERHYE PC

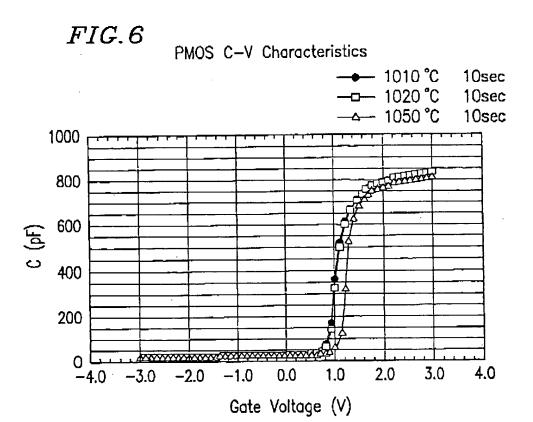
Inventor: OHMINAMI SN 10/003,258/Sheet 4 of 9 Atty. Okt.: 829-593 REPLACEMENT SHEET



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Inventor: OHMINAMI SN 10/003,258/Sheet 6 of 9 Atty. Ditt: 829-593 REPLACEMENT SHEET



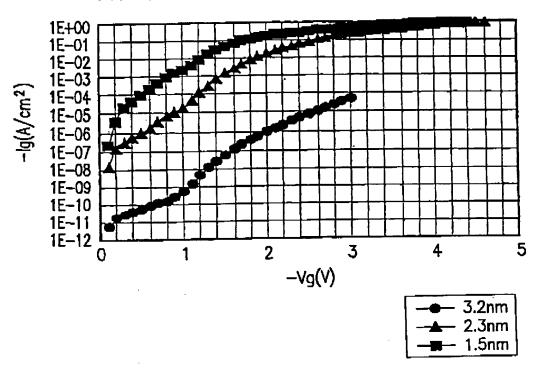
Active Area: 9E-4cm²

w/o Well Imp. Gate SiON: NO/N2

poly Si: 200nm P+lmp.: BF₂ Inventor: OHMINAMI SN 10/003,258/Sheet 7 of B Atty, Dkt.: 829-593 REPLACEMENT SHEET

FIG.7





400

200

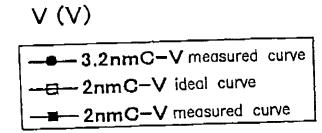
0

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FIG. 8 (PRIOR ART)
NMOS C-V Characterisics

1600
1400
1200
1000
1000
72
800
0 600
-71

0



2

P.11

Fax: 703-816-4100 inventor: Oriminami SN 10/003,258/Sheet 9 of 9 Atty. Dkt.: 829-593 REPLACEMENT SHEET

FIG.9 (PRIOR ART)